

# Phase frequency detector and charge pump

## SPECIFICATION

### 1 FEATURES

- AMS035 BiCMOS 0.35  $\mu\text{m}$
- Input signals with low amplitude
- Low disbalance of output current
- Supported foundries: TSMC, UMC, Global Foundries, SMIC, iHP, AMS, Vanguard, SiTerra

### 2 APPLICATION

- Phase-locked loop synthesizer

### 3 FUNCTIONAL DESCRIPTION

Phase-frequency detector (PFD) forms control signal for VCO tuning. PFD compares phases of divided VCO signal and divided reference oscillator signal and detects phase difference. Charge pump generates pulses for loop filter.

The block is fabricated on AMS035 BiCMOS 0.35  $\mu\text{m}$  technology.

### 4 STRUCTURE

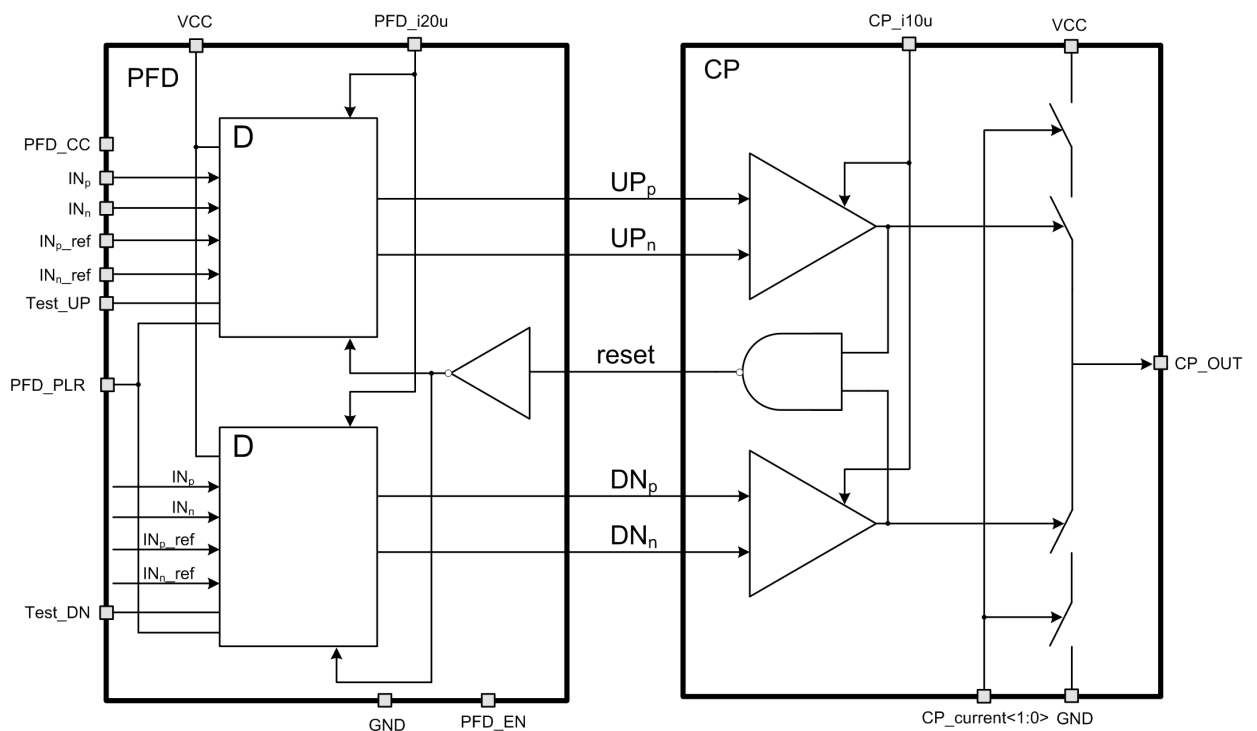


Figure 1: Phase frequency detector and charge pump structure.

## 5 PIN DESCRIPTION

Name	Direction	Description
PFD_i20u	IO	PFD reference current
CP_i10u	IO	Charge pump reference current
IN <sub>p</sub>	I	PLL VCO divided signal differential input
IN <sub>n</sub>		
IN <sub>p_ref</sub>	I	PLL reference oscillator signal differential input
IN <sub>n_ref</sub>		
PFD_EN	I	PFD and charge pump enable/disable
PFD_PLR	I	PFD polarity
PFD_CC	I	PFD current consumption control
Test_UP	I	Enable/disable of PFD up static current test mode
Test_DN	I	Enable/disable of PFD down static current test mode
CP_current<1:0>	I	Output current adjustment
CP_OUT	O	Charge pump output
GND	IO	Ground
VCC	IO	Supply voltage

## 6 LAYOUT DESCRIPTION

Frequency-phase detector and charge pump dimensions are given in the table 1.

**Table 1:** Blocks dimensions.

Dimension	Value	Unit
Height	316	$\mu\text{m}$
Width	500	$\mu\text{m}$

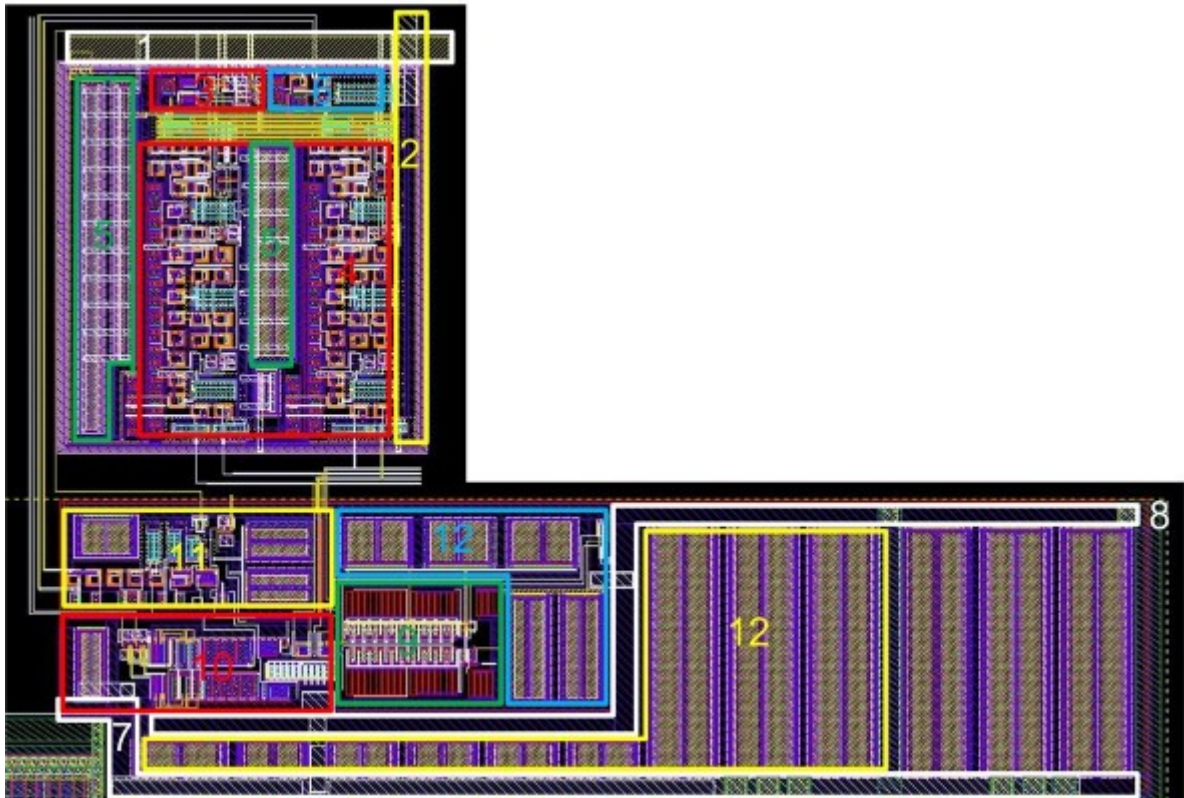


Figure 2: PFD and CP layout view.

- 1 PFD ground bus
- 2 PFD supply voltage bus
- 3 PFD input buffer
- 4 PFD triggers
- 5 PFD filter capacitors
- 6 PFD reset circuit
- 7 Charge pump ground bus
- 8 Charge pump supply voltage bus
- 9 Charge pump input buffer
- 10 Charge pump output stage
- 11 Signal former for phase detector reset circuit
- 12 Charge pump filter capacitors

## 7 OPERATING CHARACTERISTICS

### 7.1 TECHNICAL CHARACTERISTICS

Technology \_\_\_\_\_ AMS035 BiCMOS 0.35  
 Status \_\_\_\_\_ Silicon proven  
 Area \_\_\_\_\_ 0.101 mm<sup>2</sup>

### 7.2 ELECTRICAL CHARACTERISTICS

The values of electrical characteristics are specified for  $V_{cc} = 3.0 \div 3.3$  V и  $T = -40 \div +85$  °C. Typical values are at  $V_{cc} = 3.15$  V,  $T = +27$  °C, unless otherwise specified.

Parameter	Symbol	Condition	Value			Unit
			min	typ	max	
Supply voltage	$V_{CC}$	-	3.0	3.15	3.3	V
Operating temperature range	T	-	-40	+27	+85	°C
Reference frequency	$F_{ref}$	-	-	24.84	-	MHz
Peak-to-peak voltage at the differential input	$A_{in\ p-p}$	For inputs $IN_p$ , $IN_n$ , $IN_{p\_ref}$ и $IN_{n\_ref}$	0.2	-	2.0	V
DC operating point	$V_{op}$		$V_{cc} - 1.2$	-	$V_{cc} - 0.2$	V
Output current	$I_{out}$	Preset 1	19.1	19.3	20.6	μA
		Preset 2	36.8	37.4	39.6	
		Preset 3	71.4	73.0	77.4	
		Preset 4	88.7	90.7	96.3	
PFD reset time	$t_{rst}$	-	2.1	2.69	3.5	ns
Supply current	$I_{cc}$	-	1.28	1.4	1.53	mA
Stand-by current	$I_{stb}$	-	0.6	0.75	353.5	nA
Input logic-level high	$V_{IH}$	For digital inputs	$0.7V_{cc}$	-	$V_{cc} + 0.25$	V
Input logic-level low	$V_{IL}$		-0.25	-	0.3	V

## 8 DELIVERABLES

IP contents:

- Schematic or NetList
- Layout or blackbox
- Extracted view (optional)
- GDSII
- DRC, LVS, antenna report
- Test bench with saved configurations (optional)
- Documentation